

2 X 2 Crosspoint Switch for Audio Applications

Check for Samples: TS3A26746E

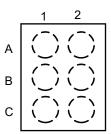
FEATURES

- Ultra Low R_{ON} for GND Switch (80-mΩ typical)
- R_{ON} for MIC Switch <10-Ω
- 3.0V to 3.6V V+ Operation
- Control Input is 1.8-V Logic Compatible
- 6-bump, 0.5mm pitch CSP Package (1.45mm × 0.95mm × 0.5mm)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 500-V Charged-Device Model (C101)
- ESD Performance (SLEEVE, RING2)
 - ±8-kV Contact Discharge (IEC 61000-4-2)

APPLICATIONS

- Cellular phones
- PDAs
- Portable Instrumentation
- Digital Still Cameras
- Portable Navigation Devices

PINOUT



DESCRIPTION

The TS3A26746E is a 2 × 2 cross-point switch that is used to interchange the Ground and MIC connections on a headphone connector. The Ground switch has an ultra low R_{ON} of <0.1 Ω to minimize voltage drop across it, preventing undesired increases in headphone ground reference voltage. The switch state is controlled via the SEL input. When SEL=High, GND is connected to RING2 and MIC is connected to SLEEVE. When SEL=Low, GND is connected to SLEEVE and MIC is connected to RING2. An internal 100k pull-up resistor on the SEL input sets the default state of the switch.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

TYPICAL APPLICATION BLOCK DIAGRAM

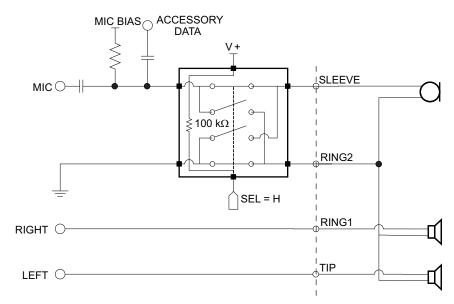


Figure 1. Standard Headphone Configuration (SEL=H)

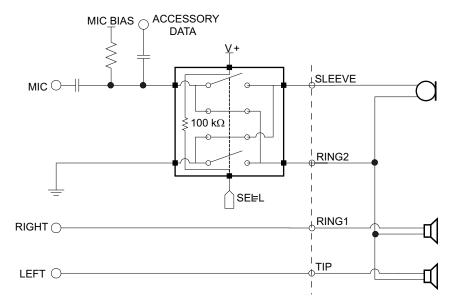
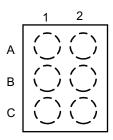


Figure 2. Alternate Headphone Configuration (SEL=L)



PINOUT



TERMINAL ASSIGNMENTS

	1	2
Α	SEL	V+
В	MIC	SLEEVE
С	GND	RING2

PIN FUNCTIONS

BALL#	PIN		DESCRIPTION				
DALL#	NAME	TYPE	'ESCRIFTION				
A1	SEL	Input	Control Input				
A2	V+	Power	Supply Voltage				
B1	MIC	I/O	MIC				
B2	SLEEV E	I/O	Sleeve Connection on Headphone Jack				
C1	GND	Ground	Ground				
C2	RING2	I/O	2 nd Ring Connection on Headphone Jack				

Table 1. FUNCTION TABLE

SEL	MIC to SLEEVE, GND to RING2	MIC to RING2, GND to SLEEVE
L	OFF	ON
Н	ON	OFF

Copyright © 2011–2013, Texas Instruments Incorporated



ABSOLUTE MAXIMUM RATINGS(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V ₊	Supply voltage range (3)		-0.3	4.0	V
V _{MIC} V _{SLEEVE} V _{RING2}	Analog voltage range ⁽³⁾				V
I _K	Analog port diode current	V _{MIC} , V _{SLEEVE} , V _{RING2} < 0 V	-50		mA
VI	Digital input voltage rang	е	-0.3	4.0	V
I _{IK}	Digital input clamp current (3)	V _I < 0 V	-50		mA
I ₊	Continuous current throu		100	mA	
I _{GND}	Continuous current through GND				mA
θ_{JA}	Package thermal impedance ⁽⁴⁾	YZP package		102	°C/W
T _{stg}	Storage temperature ran	ge	-65	150	°C

- (1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The package thermal impedance is calculated in accordance with JESD 51-7.

ELECTRICAL CHARACTERISTICS FOR 3.3 V SUPPLY⁽¹⁾

 $V_{+} = 3 \text{ V to } 3.6 \text{ V}, T_{A} = -40^{\circ}\text{C to } 85^{\circ}\text{C (unless otherwise noted)}$

PARA	AMETER	TEST CONDITIONS	TA	V_{+}	MIN	TYP	MAX	UNIT	
MIC SWITCH									
$\begin{matrix} V_{MIC}, V_{SLEEVE}, \\ V_{RING2} \end{matrix}$	Analog signal range					0		V+	V
r	ON-state	0 ≤ V _{SLEEVE} or V _{RING2} ≤ V ₊ , I _{MIC} = −32	Switch	25°C	3 V		5	8	Ω
r _{on}	resistance	mA	ON	Full				10	\$2
	ON-state	$0 \le V_{SLEEVE}$ or $V_{RING2} \le V_+$, $I_{MIC} = -32$	Switch	25°C	3 V		1	2.3	
r _{on(flat)}	resistance flatness	mA	ON	Full				2.5	Ω
I _{SLEEVE(OFF)} , SLEEVE, RING2		V _{SLEEVE} or V _{RING2} = 1 V, V _{MIC} = 3 V, or	Switch	25°C		-0.5	0.05	0.5	
I _{RING2(OFF)}	OFF leakage current	V _{SLEEVE} or V _{RING2} = 3 V, V _{MIC} = 1 V	OFF	Full	3.6 V	-2		2	μA
1	MIC OFF leakage		Switch	witch 25°C	3.6 V	-1	0.1	1	
I _{MIC(OFF)}	current	V _{SLEEVE} or V _{RING2} = 1 V, V _{MIC} = 3 V	OFF	Full		-2		2	μA
I _{SLEEVE(ON)} , SLEEVE, RING2 ON leakage current		V _{SLEEVE} or V _{RING2} = 1 V, V _{MIC} = Open, or	Switch	25°C		-2	0.5	2	
		V _{SLEEVE} or V _{RING2} = 3 V, V _{MIC} = Open		Full	3.6 V	-2		2	μA
I _{MIC(ON)} MIC ON leakage current		V _{SLEEVE} or V _{RING2} = Open V, V _{MIC} = 1 V,	Switch	25°C	3.6 V	-2	0.5	2	
		or V_{SLEEVE} or V_{RING2} = Open, V_{MIC} = 3 V	ON	Full	3.0 V	-2		2	μΑ
GND SWITCH				·					
	ON-state	I _{SLEEVE} or I _{RING2} = +32 mA, V _{GND} = 0 V,	Switch	25°C	3 V		0.08	0.09	
r _{on}	resistance	$I_{GND} = -32 \text{ mA}$	ON	Full				0.11	Ω
I _{SLEEVE(OFF)} ,		V 27 V 27 AV 0 V		25°C	3.6 V	-0.5	0.05	0.5	
I _{RING2(OFF)}	SLEEVE, RING2	V_{SLEEVE} or $V_{RING2} = 3V$ and $V_{GND} = 0 V$	OFF	Full	3.0 V	-1		1	μA
I _{SLEEVE(PWROFF}	OFF leakage current V _{SI EEVE} or V _{RING2} = 0 to 3.6 V and V _{GND}		Switch	25°C		-1	0.5	1	
), I _{RING2(PWROFF))}	Ouron	rent V_{SLEEVE} or $V_{RING2} = 0$ to 3.6 V and V_{GND} = 0 V		Full	0 V	-10		10	μA

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Submit Documentation Feedback

Copyright © 2011–2013, Texas Instruments Incorporated



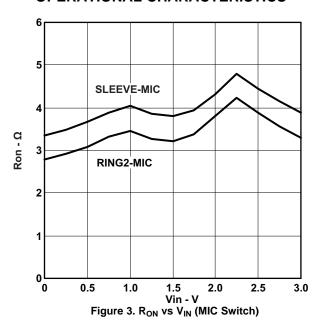
ELECTRICAL CHARACTERISTICS FOR 3.3 V SUPPLY⁽¹⁾ (continued)

 $V_{+} = 3 \text{ V}$ to 3.6 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

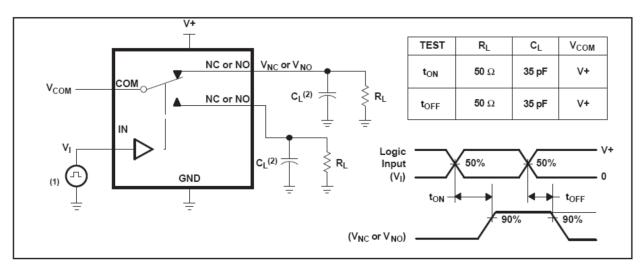
PARAMETER		TEST CONDITION	TA	V_{+}	MIN	TYP	MAX	UNIT	
DIGITAL C	ONTROL INPUTS (SEL)							
V _{IH}	Input logic high			Full	3.6 V	1.2		3.6	V
V _{IL}	Input logic low			Full	3.6 V	0		0.4	V
L	Input logic high	$V_I = V_+$		25°C	3.6 V	-1	0.05	1	μA
I _{IH}	leakage current	VI = V+		Full		-2		2	μΑ
I _{IL}	Input logic low leakage current	V _I = 0 V		25°C	3.6 V	-38	-36	-34	μA
	leakage current		Full		-4 5		-30		
DYNAMIC		T		1 1					
		V D 50.0	C ₁ = 35	25°C	3.3 V		150	200	
t _{ON}	Turn-on time	$V_{\text{MIC}} = V_{+}, R_{\text{L}} = 50 \ \Omega$ $C_{\text{L}} = 35 \ \text{pF}$		Full	3 V to 3.6 V			250	ns
			C - 25	25°C	3.3 V		5	10	
t _{OFF}	Turn-off time	$V_{MIC} = V_{+}, R_{L} = 50 \Omega$ $C_{L} = 38$ pF		Full	3 V to 3.6 V			15	ns
	Duranta haɗa wa	25°C			3.3 V	70		330	ns
t _{BBM}	Break-before- make time	$V_{MIC} = V_{+}$	Full		3 V to 3.6 V			330	
C _{MIC}	MIC capacitance	SEL=High	25°C		3.3 V		100	140	pF
		SEL=Low	25°C		3.3 V		100	140	pF
0	SLEEVE / RING2	SEL=High	25°C		3.3 V		100	140	pF
C _{SLEEVE}	capacitance	SEL=Low		3.3 V		100	140	pF	
C _I	Digital input capacitance	V _I = V ₊ or 0 V		3.3 V		4.0		pF	
THD	Total harmonic distortion	$R_L = 1k \Omega$, $V = 30 \text{ mVPP}$	25°C	3.3 V		0.01%			
SUPPLY			•						
V+	Power Supply Voltage					3.0	3.3	3.6	V
		$V_I = V_+$			3.6 V		0.01	1	
	Positive supply							5	μA
I ₊	current	V _I = 0 V					40	41	
								50	μA



OPERATIONAL CHARACTERISTICS



PARAMETER MEASRUMENT INFORMATION

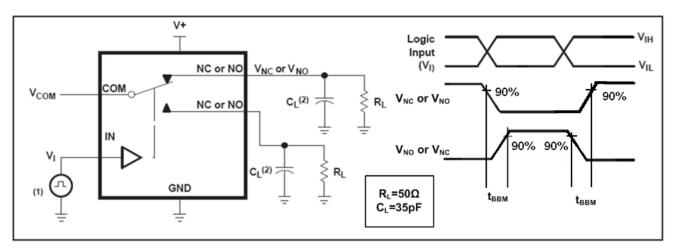


- A. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_r < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 4. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



PARAMETER MEASRUMENT INFORMATION (continued)



- C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 5 ns.

Figure 5. Break-Before-Make Time (t_{BBM})



REVISION HISTORY

Cł	hanges from Revision B (November 2011) to Revision C	Page
•	Replaced 1 page preview with full document.	



PACKAGE OPTION ADDENDUM

23-May-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	_	Pins	U	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	D	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)			(4/5)	
TS3A26746EYZPR	ACTIVE	DSBGA	YZP	6	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	7N		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

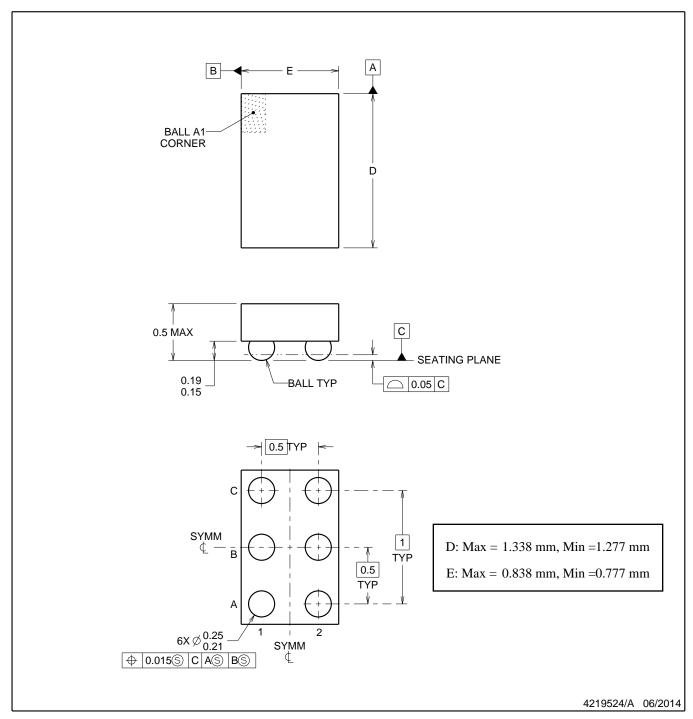
- (3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



DIE SIZE BALL GRID ARRAY



NOTES:

NanoFree Is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. NanoFree[™] package configuration.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
 For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



IMPORTANT NOTICE FOR TI DESIGN INFORMATION AND RESOURCES

Texas Instruments Incorporated ("TI") technical, application or other design advice, services or information, including, but not limited to, reference designs and materials relating to evaluation modules, (collectively, "TI Resources") are intended to assist designers who are developing applications that incorporate TI products; by downloading, accessing or using any particular TI Resource in any way, you (individually or, if you are acting on behalf of a company, your company) agree to use it solely for this purpose and subject to the terms of this Notice.

TI's provision of TI Resources does not expand or otherwise alter TI's applicable published warranties or warranty disclaimers for TI products, and no additional obligations or liabilities arise from TI providing such TI Resources. TI reserves the right to make corrections, enhancements, improvements and other changes to its TI Resources.

You understand and agree that you remain responsible for using your independent analysis, evaluation and judgment in designing your applications and that you have full and exclusive responsibility to assure the safety of your applications and compliance of your applications (and of all TI products used in or for your applications) with all applicable regulations, laws and other applicable requirements. You represent that, with respect to your applications, you have all the necessary expertise to create and implement safeguards that (1) anticipate dangerous consequences of failures, (2) monitor failures and their consequences, and (3) lessen the likelihood of failures that might cause harm and take appropriate actions. You agree that prior to using or distributing any applications that include TI products, you will thoroughly test such applications and the functionality of such TI products as used in such applications. TI has not conducted any testing other than that specifically described in the published documentation for a particular TI Resource.

You are authorized to use, copy and modify any individual TI Resource only in connection with the development of applications that include the TI product(s) identified in such TI Resource. NO OTHER LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE TO ANY OTHER TI INTELLECTUAL PROPERTY RIGHT, AND NO LICENSE TO ANY TECHNOLOGY OR INTELLECTUAL PROPERTY RIGHT OF TI OR ANY THIRD PARTY IS GRANTED HEREIN, including but not limited to any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information regarding or referencing third-party products or services does not constitute a license to use such products or services, or a warranty or endorsement thereof. Use of TI Resources may require a license from a third party under the patents or other intellectual property of TI.

TI RESOURCES ARE PROVIDED "AS IS" AND WITH ALL FAULTS. TI DISCLAIMS ALL OTHER WARRANTIES OR REPRESENTATIONS, EXPRESS OR IMPLIED, REGARDING TI RESOURCES OR USE THEREOF, INCLUDING BUT NOT LIMITED TO ACCURACY OR COMPLETENESS, TITLE, ANY EPIDEMIC FAILURE WARRANTY AND ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, AND NON-INFRINGEMENT OF ANY THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

TI SHALL NOT BE LIABLE FOR AND SHALL NOT DEFEND OR INDEMNIFY YOU AGAINST ANY CLAIM, INCLUDING BUT NOT LIMITED TO ANY INFRINGEMENT CLAIM THAT RELATES TO OR IS BASED ON ANY COMBINATION OF PRODUCTS EVEN IF DESCRIBED IN TI RESOURCES OR OTHERWISE. IN NO EVENT SHALL TI BE LIABLE FOR ANY ACTUAL, DIRECT, SPECIAL, COLLATERAL, INDIRECT, PUNITIVE, INCIDENTAL, CONSEQUENTIAL OR EXEMPLARY DAMAGES IN CONNECTION WITH OR ARISING OUT OF TI RESOURCES OR USE THEREOF, AND REGARDLESS OF WHETHER TI HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES.

You agree to fully indemnify TI and its representatives against any damages, costs, losses, and/or liabilities arising out of your non-compliance with the terms and provisions of this Notice.

This Notice applies to TI Resources. Additional terms apply to the use and purchase of certain types of materials, TI products and services. These include; without limitation, TI's standard terms for semiconductor products http://www.ti.com/sc/docs/stdterms.htm), evaluation modules, and samples (http://www.ti.com/sc/docs/sampterms.htm).

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2017, Texas Instruments Incorporated